

Direct Reactions of Solids

**"HEAT-AND-BEAT" or "SHAKE-AND-BAKE"
Solid state reactions**

At least one of the reactants and one of the products are solid

Reactions in a lattice of atoms

Atomic mobility

High temperatures

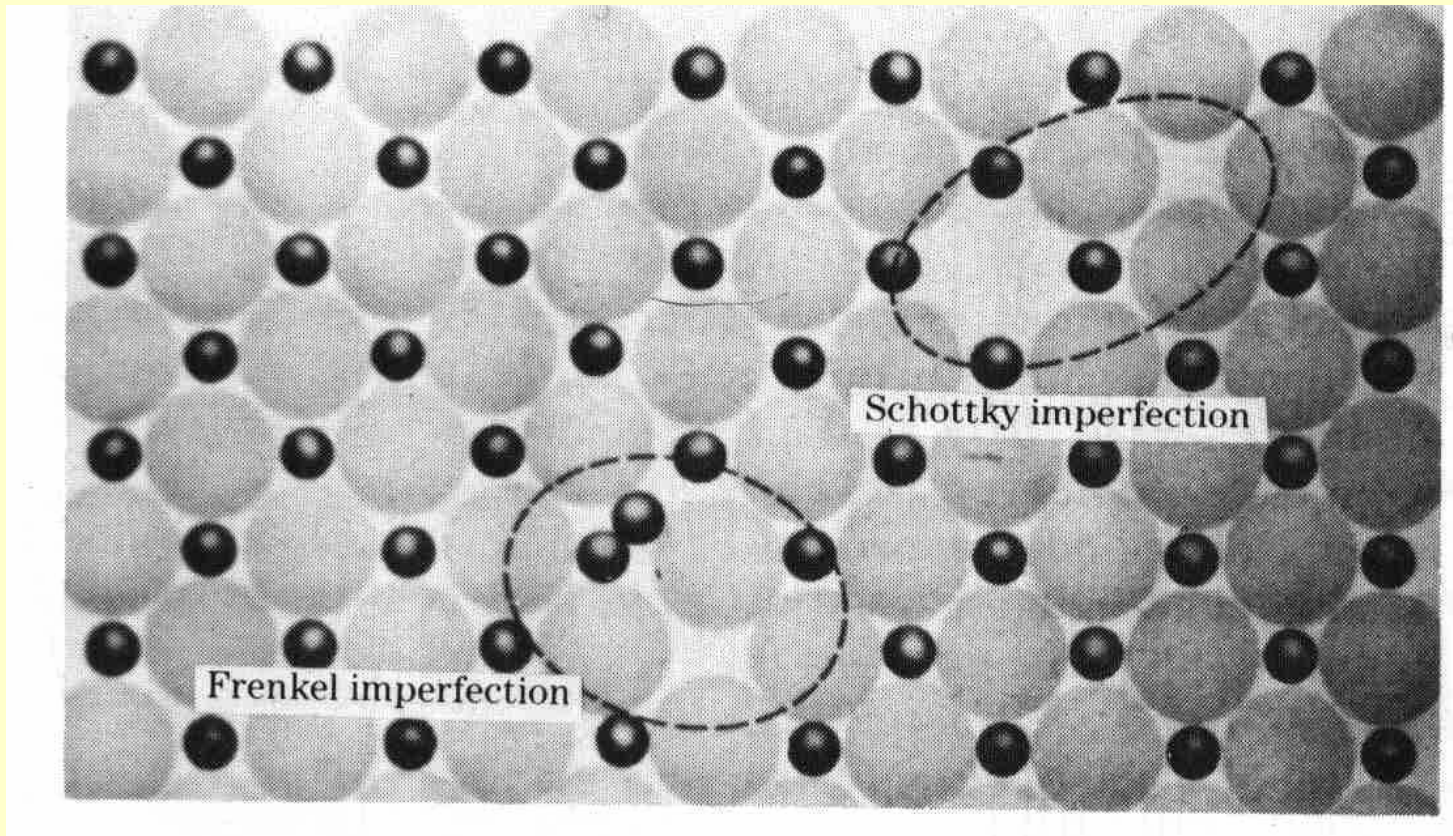
No mobility without defects – perfect crystal = no chemistry

Reactions on the interphase between phases

Microstructure

Diffusion controls the reaction rate

Point Defects

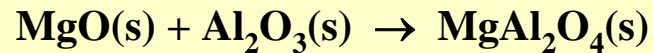
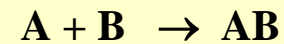


Schottky-imperfection: vacancy, missing ions moved to the surface

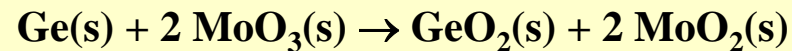
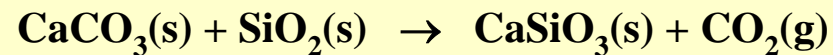
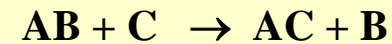
Frenkel-imperfection: vacancy, missing ions on interstitial positions

Reaction Types

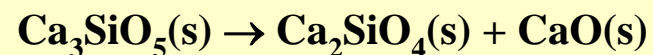
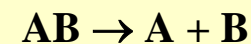
Solid - solid synthesis - addition



Solid - solid synthesis – exchange, metathesis

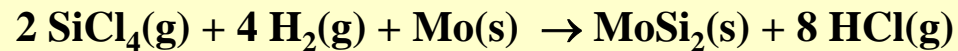
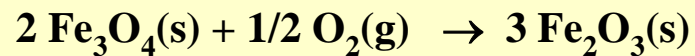


Solid - solid synthesis - dissociation



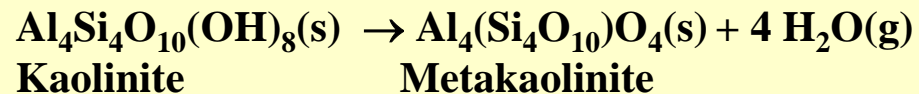
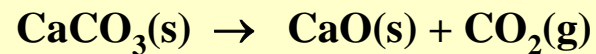
Reaction Types

Solid – gas synthesis **A + B → AB**



High temperature corrosion of metals in air

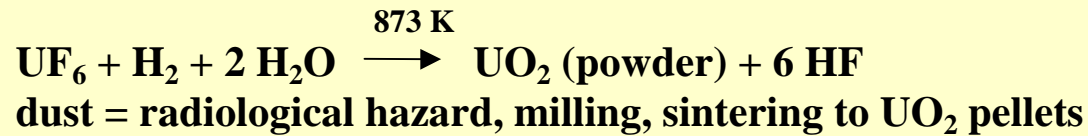
Solid – gas dissociation **AB → A + B**



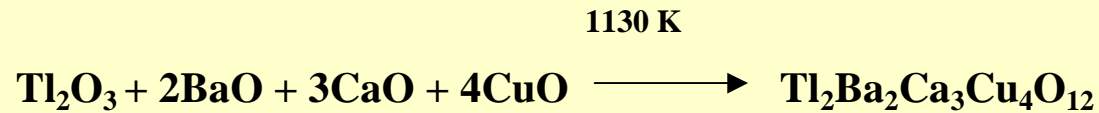
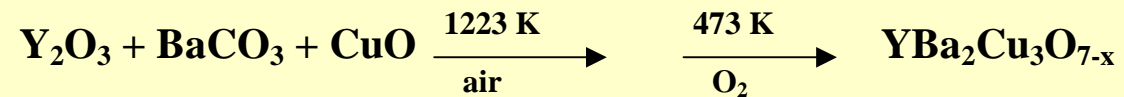
Direct Reactions of Solids

Other Examples

Oxides



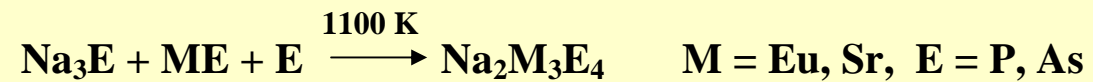
YBCO 123 Superconductor (1987)



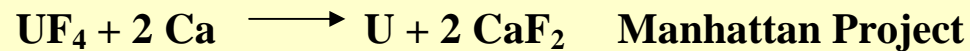
Direct Reactions of Solids

Other classes than oxides

Pnictides

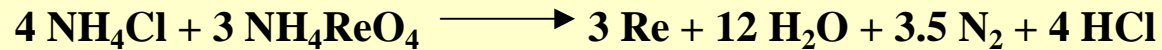
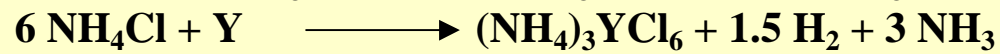
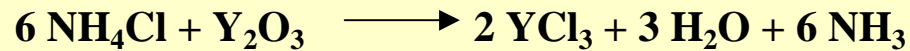
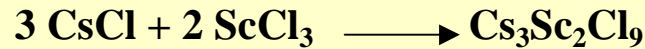


Metals

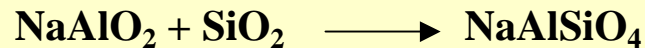


Direct Reactions of Solids

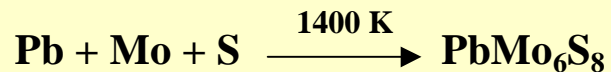
Chlorides



Aluminosilicates



Chalcogenides



Chevrel phases

($\text{ M}_x\text{ Mo}_6\text{ X}_8$, $\text{ M} = \text{ RE, Sn, Pb, Cu}$,
 $\text{ X} = \text{ S, Se, Te}$)

Direct Reactions of Solids

Powder Mixing Method

Precise weighing for exact stoichiometry

Mixing (components, dopants, additives)

Milling or grinding (ball mill, mortar)

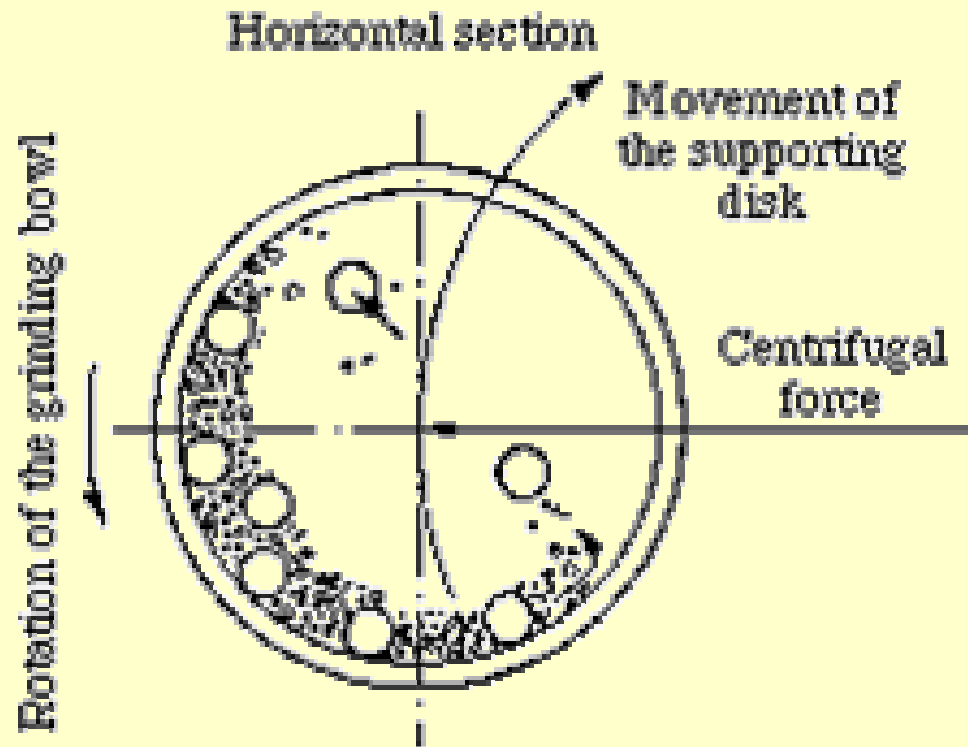
Compaction (pelleting, organic binders)

Calcination @ high temperature (> 1000 °C)

Firing/grinding cycles

DIRECT REACTION OF SOLIDS

Planetary ball mill



Direct Reactions of Solids

Advantages

- simple equipment
- low cost and easily accessible starting materials
- well studied

Disadvantages

- impurities from grinding (Fe, Cr, ...)
- broad particle size distribution
- some phases unstable @ high T, decomposition
- formation of undesirable phases
- slow formation, diffusion, long reaction times
- large grain size
- poor chemical homogeneity:
 - poor mixing of large crystallites
(milling lower limit ~ 100 nm)
 - volatility of some components (Na₂O, PbO, ...)
 - uptake of ambient gas (O₂ in superconductors)

Direct Reactions of Solids

Experimental Considerations

☛ Reagents

Drying, fine grain powders for maximum SA, surface activation (Mo + H₂), in situ decomposition (CO₃²⁻, OH⁻, O₂²⁻, C₂O₄²⁻) for intimate mixing, precursor reagents, homogenization, organic solvents, grinding, ball milling, ultrasonication

☛ Container Materials

Chemically inert crucibles, boats, ampoules (open, sealed, welded)

Noble metals: Au, Ag, Pt, Ni, Rh, Ir, Nb, Ta, Mo, W

Refractories: alumina, zirconia, silica, BN, graphite

Reactivities with containers at high temperatures needs to be carefully evaluated for each system, pelleting minimizes contact with container, sacrificial pellet

Properties of Common Container Materials

Material	Maximum Working Temp., K	Thermal Shock Resistance	Thermal Conductivity, $W m^{-1} K^{-1}$	Coefficient of Linear Expansion $\times 10^6, K^{-1}$	Other Properties
Pyrex	770	GOOD	1.13	3.2	Permeable to air at high T
CaF ₂	1420	FAIR	-	24	-
SiO ₂	1530	VERY GOOD	1.38 - 2.67	0.4 - 0.6	Permeable to air at high T, devitrification above 1670 K
Si ₃ N ₄	1770	FAIR	10 - 33	6.4	-
Pt	1950	VERY GOOD	73	9.11	Plastic at high T
BN	1970	VERY GOOD	5.02	0.2-3	Oxidizes in air above 970 K
Vitreous C	2070	GOOD	4.19 - 8.37	2-3.5	Oxidizes in air above 900 K
Al ₂ O ₃	2170	FAIR	35 - 39	8	Reacts with metals above 1800 K
AlN	2270	FAIR	50 - 170	5.7	-
BeO	2570	GOOD	230	8.4	Reacts with metals above 1800 K
ZrO ₂	2570	GOOD	1.97	4.5	-
Ir	2600	VERY GOOD	148	6.8	-
MgO	2870	FAIR	37.7	25	High vapor pressure
ThO ₂	3070	FAIR	4.19	6	Reacts with C above 2290 K

Direct Reactions of Solids

☛ Heating Program

Slow or fast heating, cooling, holding at a set point temperature

Tammann's rule: $T_r > 2/3 T_m$

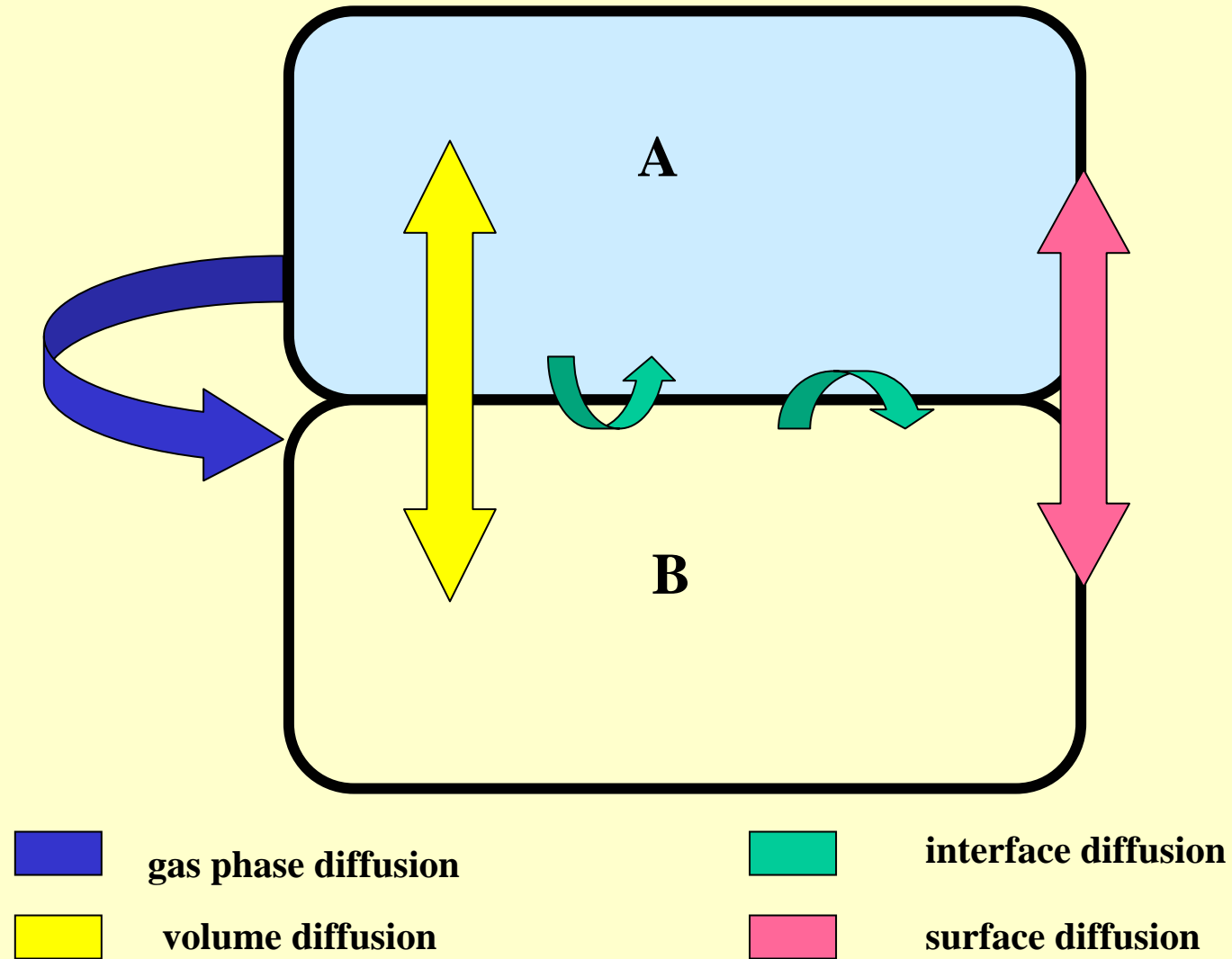
Furnaces, RF, microwave, lasers, ion or electron beam

☛ Prior decomposition

Initial cycle at lower temperature to prevent spillage or volatilization, frequent cycles of heating, cooling, grinding, boost SA. Overcoming sintering, grain growth, fresh surfaces. Pelleting, hot pressing, enhanced contact area increases rate and extent of reaction

☛ Controlled atmosphere (oxidizing, reducing, inert) or vacuum. Unstable oxidation states, preferential component volatilization if T too high, composition dependent atmosphere (O_2 , NH_3 , H_2S , ...)

Possible reaction paths between two solid grains A and B



Direct Reactions of Solids

Thermodynamic and kinetic factors

General kinetic expression

$$g(\alpha) = \int k(T) dt \quad g(\alpha) = k(T) t$$

α – the molar fraction of the reacted product at a time t

$k(T)$ – the rate constant of the process

Experimentally evaluate α at different t

Fit data into a $g(\alpha) = k(T) t$ expression to obtain $k(T)$ and the type of mechanism model

$$\alpha = \frac{P_t - P_0}{P_e - P_0}$$

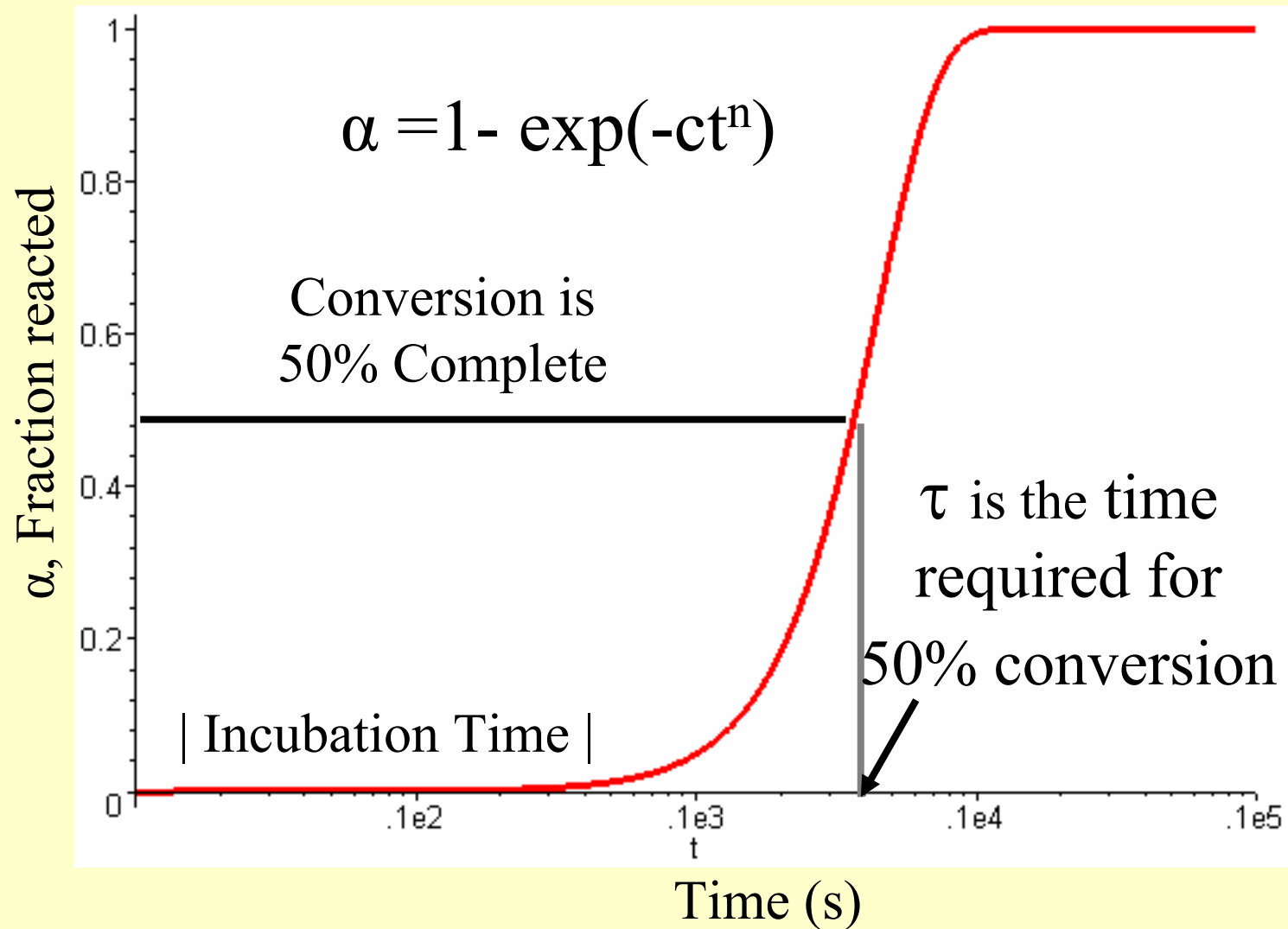
P_t = the value of a property at time t

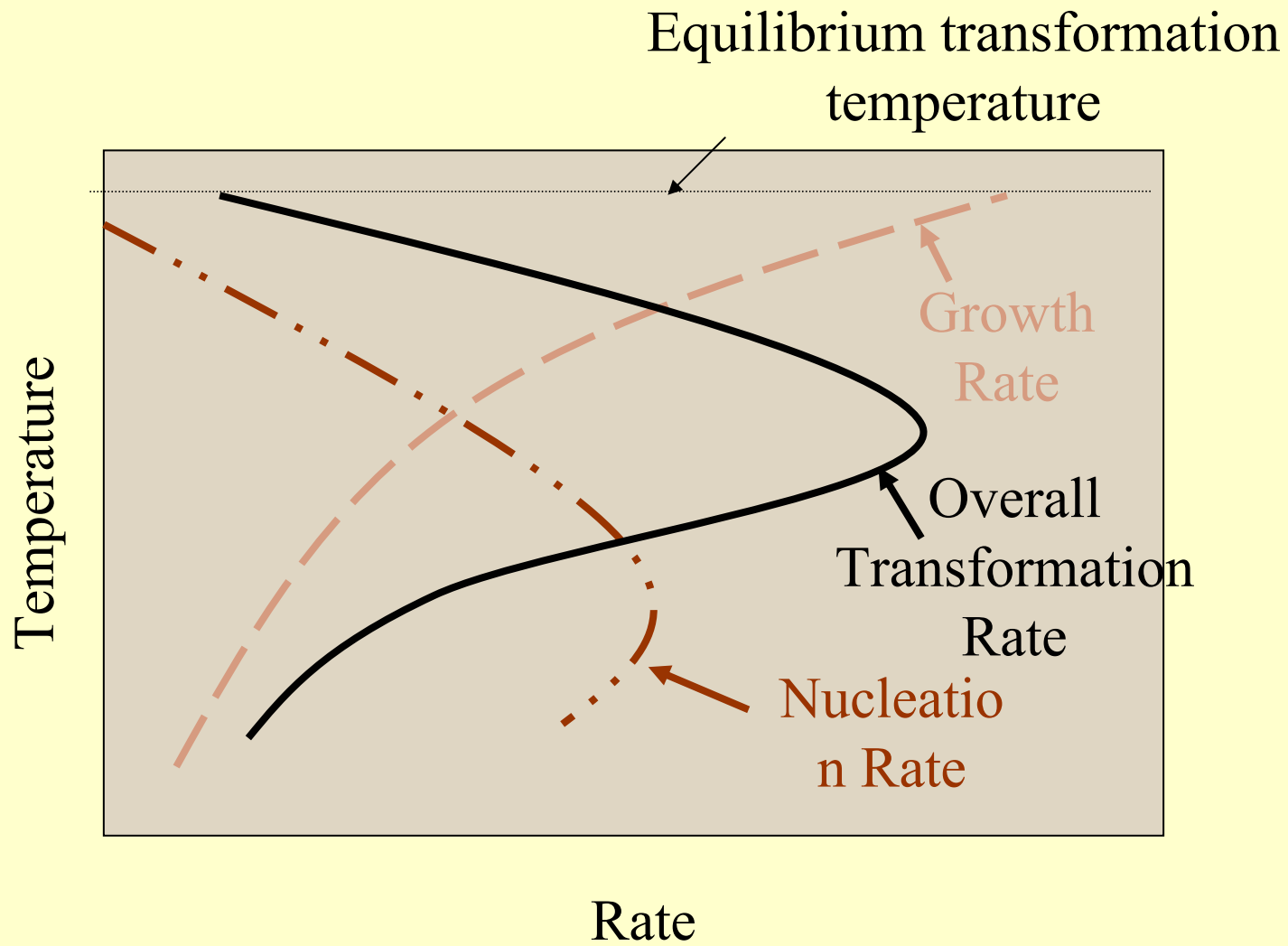
P_0 = the value of a property at the beginning

P_e = the value of a property at the end

Mechanism model	$g(\alpha)$
Diffusion controlled	
One-dimensional	α^2
Two-dimensional	$\alpha + (1 - \alpha) \ln (1 - \alpha)$
Three-dimensional, Jander	$[1 - (1 - \alpha)^{1/3}]^{2/3}$
Three-dimensional, Ginstling	$(1 - 2/3\alpha) - (1 - \alpha)^{2/3}$
Three-dimensional, Carter	$(1 + \alpha)^{2/3} + (1 - \alpha)^{2/3}$
Growth controlled	
General	$[1 - (1 - \alpha)^{1-n}]$
First order, $n = 1$	$[- \ln (1 - \alpha)]$
Nucleation controlled	
Power law	$\alpha^{1/n}$
Nucleation-Growth controlled	
Avrami	$[- \ln (1 - \alpha)]^{1/2}$
Erofeev	$[- \ln (1 - \alpha)]^{1/3}$
Planar boundary	$1 - (1 - \alpha)^{1/2}$
Spherical boundary	$1 - (1 - \alpha)^{1/3}$

Avrami Plot





Direct Reactions of Solids

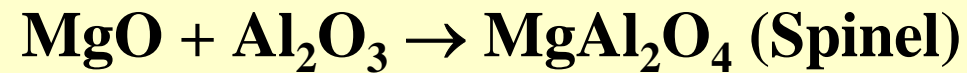
Perform the measurements in a range of temperatures T

use Arrhenius equation to evaluate the activation energy E_a

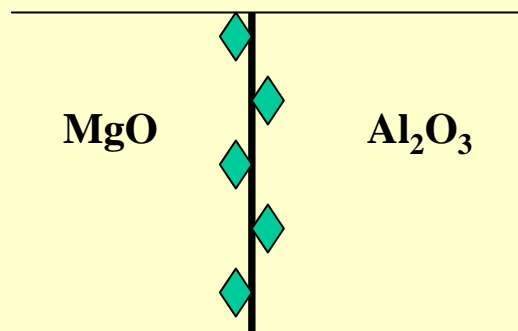
$$k(T) = k_0 \exp(-E_a/RT)$$

Direct Reactions of Solids

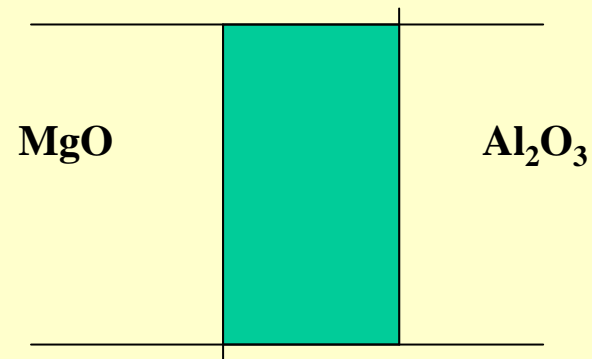
Model for a classical solid-solid reaction (below melting point !):
Planar interface between two crystals



Phase 1:
nucleation

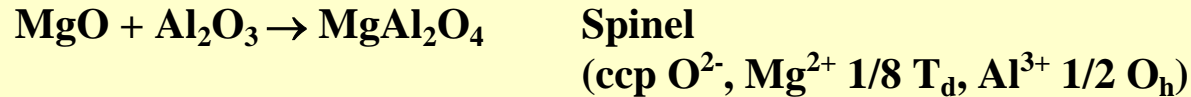


Phase 2:
growth of nuclei



Direct Reactions of Solids

Model reaction, well studied:



Single crystals of precursors, interfaces between reactant grains

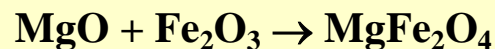
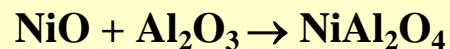
On reaction, new reactant-product MgO/MgAl₂O₄ and Al₂O₃/MgAl₂O₄ interfaces are formed

Free energy negative, favors reaction but extremely slow at normal temperatures (several days at 1500 °C)

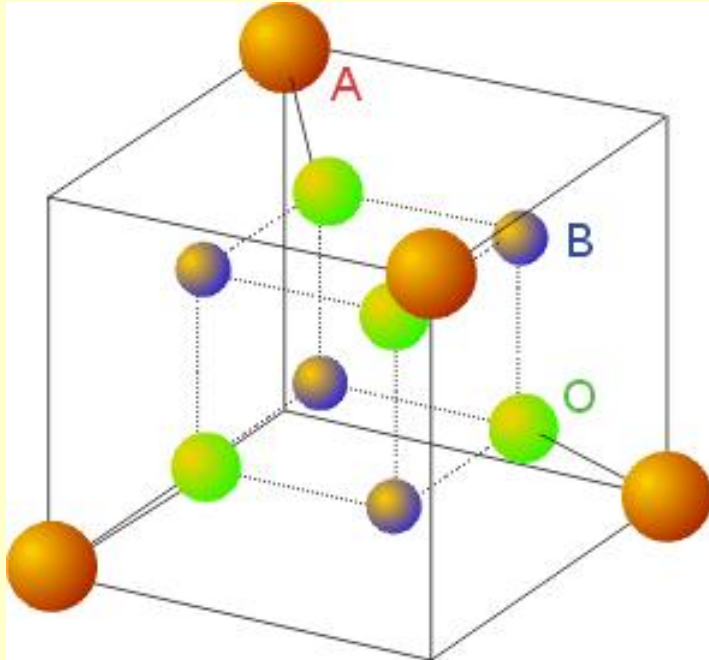
Interfacial growth rates 3 : 1

Linear dependence of interface thickness x^2 versus t

Easily monitored rates with colored product at interface, T and t



The Spinel Structure: AB_2O_4



fcc array of O^{2-} ions, A occupies 1/8 of the tetrahedral and B 1/2 of the octahedral holes

→ normal spinel: AB_2O_4

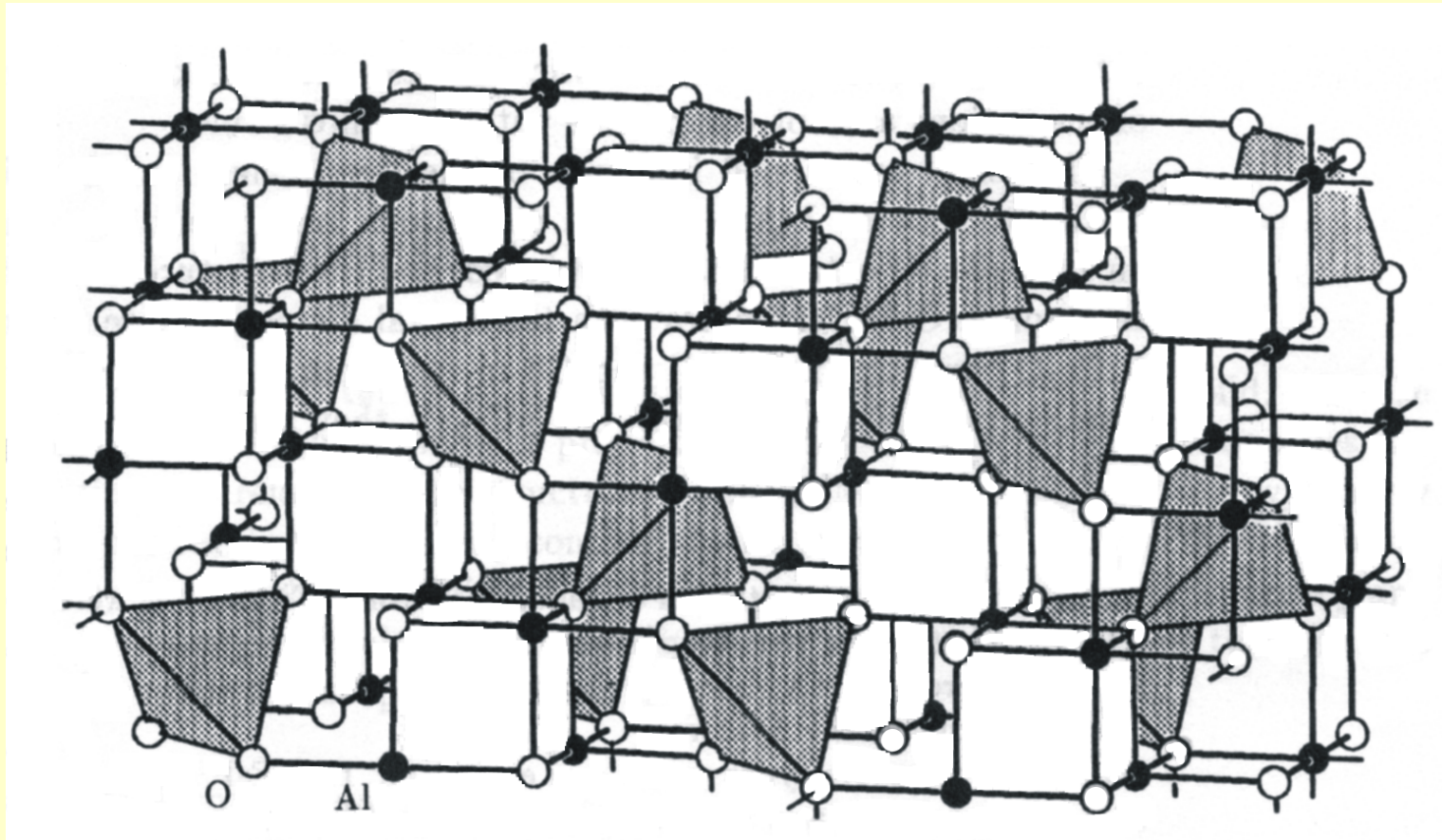
Co_3O_4 , $GeNi_2O_4$, WNa_2O_4

→ inverse spinel: $B[AB]O_4$

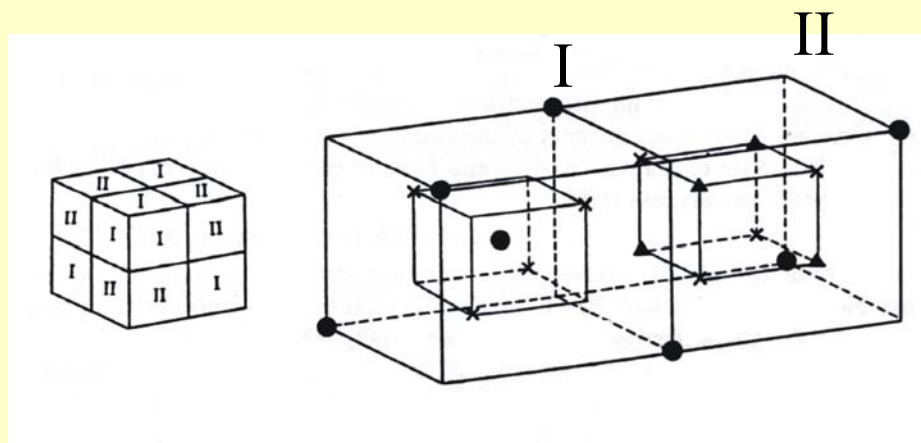
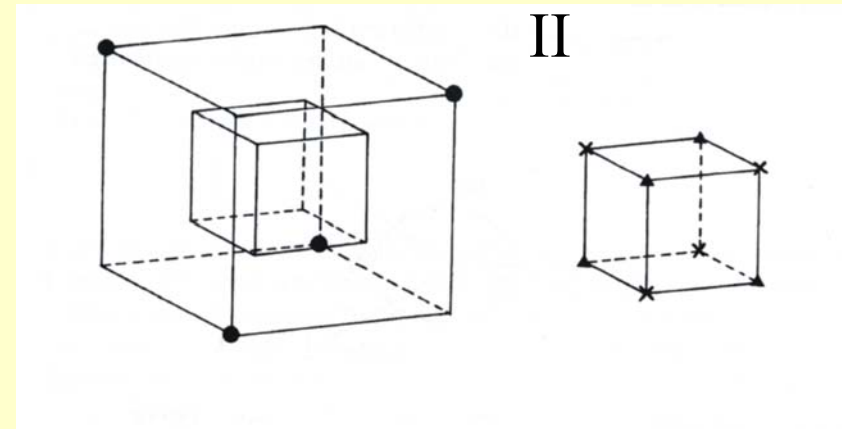
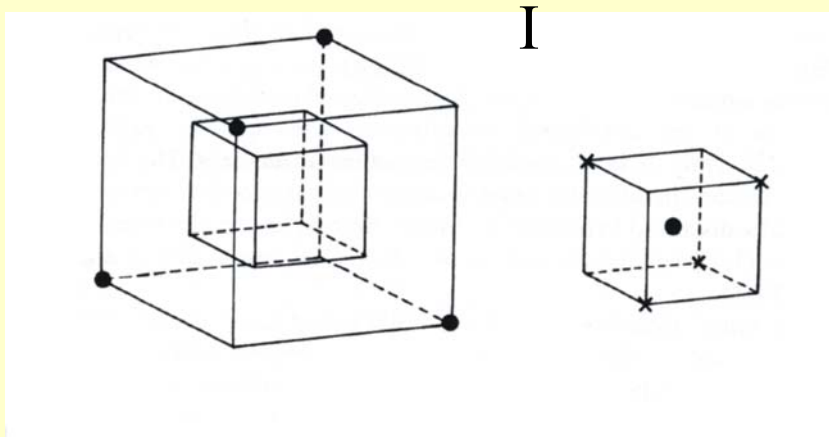
Fe_3O_4 : $Fe^{3+}[Fe^{2+}Fe^{3+}]O_4$, $TiMg_2O_4$, $NiLi_2F_4$

→ basis structure for several magnetic materials

The spinel structure: MgAl_2O_4



The spinel structure: MgAl_2O_4



• = Mg

x = O

▲ = Al

Direct Reactions of Solids

Why is nucleation, mass transport so difficult?

MgO ccp O^{2-} , Mg^{2+} in O_h sites

Al_2O_3 hcp O^{2-} , Al^{3+} in $2/3 O_h$ sites

$MgAl_2O_4$ ccp O^{2-} , Mg^{2+} $1/8 T_d$, Al^{3+} $1/2 O_h$

- ☛ Structural differences between reactants and products, major structural reorganization in forming product spinel
- ☛ Making and breaking many strong bonds (mainly ionic), high temperature process as $D(Mg^{2+})$ and $D(Al^{3+})$ large for small highly charged cations
- ☛ Long range counter-diffusion of Mg^{2+} and Al^{3+} cations across interface, usually RDS (= rate determining step), requires ionic conductivity, substitutional or interstitial hopping of cations from site to site to effect mass transport
- ☛ Nucleation of product spinel at interface, ions diffuse across thickening interface, oxide ion reorganization at nucleation site
- ☛ Decreasing rate as spinel product layer thickens

Parabolic rate law: $dx/dt = k/x$

$$x^2 = kt$$

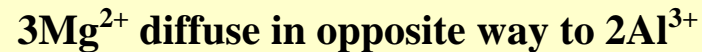
Direct Reactions of Solids

Kinetics:

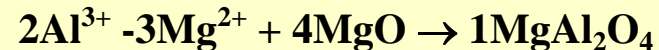
Linear x^2 vs. t plots observed

$\ln k$ vs. $1/T$ experiments provide Arrhenius activation energy E_a for the solid-state reaction

Reaction mechanism requires charge balance to be maintained in the solid state interfacial reaction:



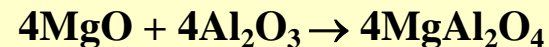
MgO/MgAl₂O₄ Interface:



MgAl₂O₄/Al₂O₃ Interface:



Overall Reaction:



the **Kirkendall** Effect : RHS/LHS growth rate of interface = 3/1

FACTORS INFLUENCING REACTIONS OF SOLIDS

CONTACT AREA

- ★ Surface area of reactants
- ★ Particle size
- ★ Pelleting, pressing, precursors

DIFFUSION RATE

- ★ Diffusion rates of atoms, ions, molecules in solids
- ★ Reaction temperature, pressure, atmosphere
- ★ Diffusion length, particle size
- ★ Defect concentration, defect type
- ★ Reaction mechanism

NUCLEATION RATE

- ★ Nucleation of product phase within the reactant with similar crystal structure
- ★ Epitactic and topotactic reactions
- ★ Surface structure and reactivity of different crystal planes/faces

Direct Reactions of Solids

KEY FACTORS IN SOLID STATE SYNTHESIS

CONTACT AREA and surface area (SA) of reacting solids control:

→ Rates of diffusion of ions through various phases, reactants and products

→ Rate of nucleation of the product phase

Reaction rate is greatly influenced by the SA of precursors as contact area depends roughly on SA of the particles

Surface Area (SA) of Precursors

spherical particles, radius r [nm], density ρ [g/cm³]

$$SA = A/m = \frac{4\pi r^2}{\frac{4}{3}\pi r^3 \cdot \rho} = 3000/r\rho \quad [m^2/g]$$

Direct Reactions of Solids

Consider 1 g of a material, density 1.0 g/cm^3 , cubic crystallites

number of cubes	edge length, cm	SA, m^2/g
1	1	$6 \cdot 10^{-4}$
10^9	10^{-3}	0.6
10^{18}	10^{-6}	600

Contact area

not in reaction rate expression for product layer thickness versus time: $dx/dt = k/x$

But for a constant product volume

$x \propto 1/A_{\text{contact}}$ and furthermore $A_{\text{contact}} \propto 1/d_{\text{particle}}$

Thus particle sizes and surface area inextricably connected and obviously $x \propto d$ and SA particle size affect the interfacial thickness

Direct Reactions of Solids

These relations suggest some strategies for rate enhancement in direct reactions:

→ Hot pressing densification of particles

**High pressure squeezing of reactive powders into pellets (700 atm)
Pressed pellets still 20-40% porous. Hot pressing improves densification**

→ Atomic mixing in composite precursor compounds

→ Coated particle mixed component reagents, corona/core precursors

→ Decreasing particle size, nanocrystalline precursors

Aimed to increase interfacial reaction area A and decrease interface thickness x , minimizes diffusion length scales

$$dx/dt = k/x = k'A = k''/d$$

DIRECT REACTION OF SOLIDS

DIFFUSION RATE

Fick's law $J = -D(dc/dx)$

J = flux of diffusing species, $\#/cm^2s$

(dc/dx) = concentration gradient, $\#/cm^4$

D = diffusion coefficient, cm^2/s , for good reaction rates $> 10^{-12}$

D increases with temperature, rapidly as you approach the melting point

Tammann's rule: Extensive reaction will not occur until the temperature reaches at least 2/3 of the melting point of one or more of the reactants.

Factors influencing cation diffusion rates:

→ Charge, mass and temperature

→ Interstitial versus substitutional diffusion

→ Number and types of defects in reactant and product phases

All types of defects enhance diffusion of ions

(intrinsic or extrinsic, vacancies, interstitials, lines, planes, dislocations, grain boundaries)

Direct Reactions of Solids

Typical diffusion coefficients for ions (atoms) in a solid at room temperature

$$10^{-13} \text{ cm}^2 \text{ s}^{-1}$$

In solid state ionic conductors (e.g. Ag-ions in α -AgI) the values are greater by orders of magnitude ($\approx 10^{-6} \text{ cm}^2 \text{ s}^{-1}$)

Knowledge of D allows an estimation of the average diffusion length for the migrating particles:

$$\langle x^2 \rangle = 2Dt \quad (\langle x^2 \rangle: \text{average square of diffusion area; } t: \text{time})$$

Diffusion

Diffusion coefficients show an exponential temperature dependence (Arrhenius type):

$$D = D_{\infty} \exp(-Q/kT)$$

D_{∞} : D for $T \rightarrow \infty$,

Q: activation energy of diffusion

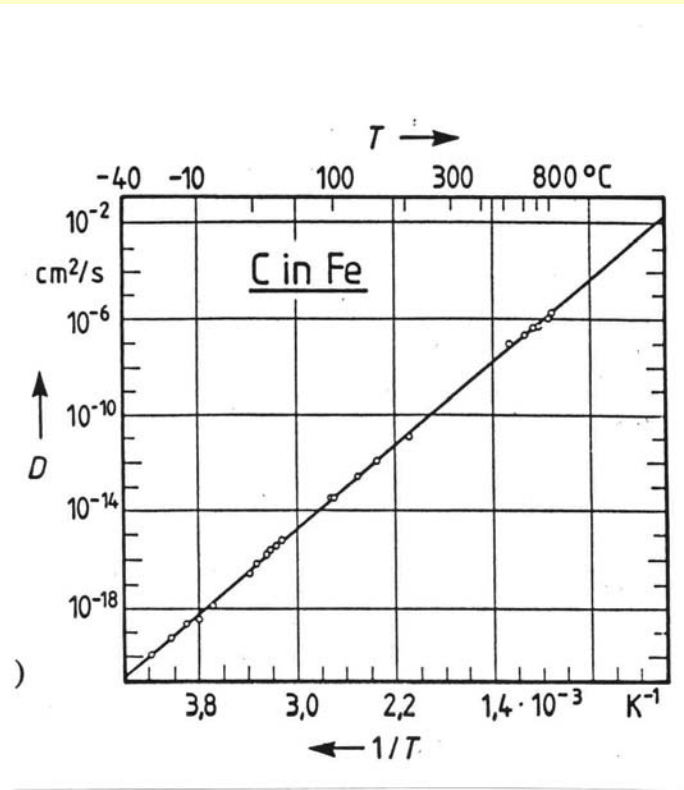
k: Boltzmann constant

The logarithmic representation of D versus $1/T$ is linear

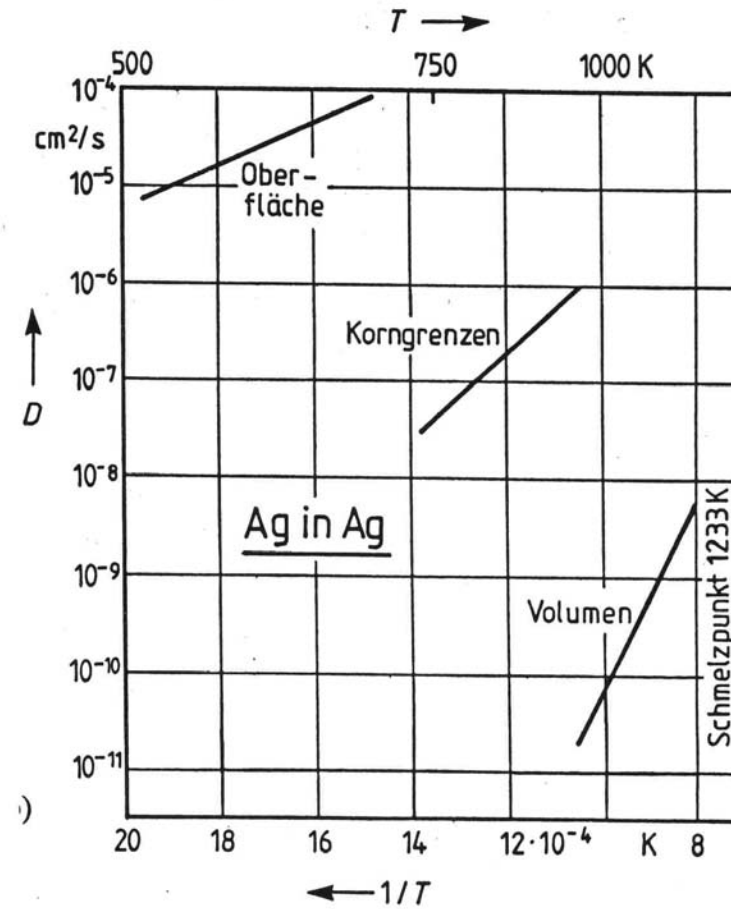
the slope corresponds to the activation energy Q and the intercept to D_{∞} .

Diffusion

C in Fe



Ag in Ag



Direct Reactions of Solids

NUCLEATION RATE

$$\text{Nucleation rate} = \text{const.} \times \exp\{- (\Delta G_N + \Delta G_D)/kT\}$$

ΔG_N = thermodynamic barrier to nucleation

ΔG_D = kinetic barrier to diffusion across the liquid/nucleus interface

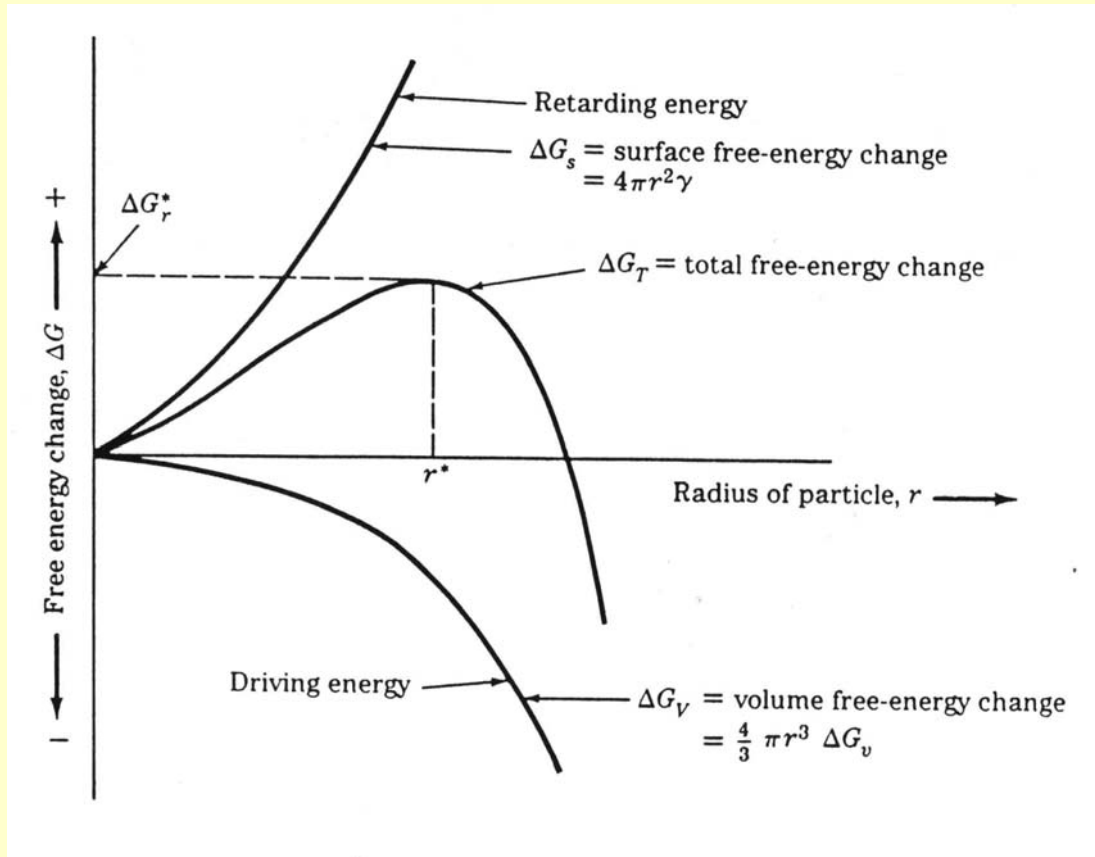
$$\Delta G_N = \Delta G_S + 4/3\pi r^3 \Delta G_V$$

$\Delta G_S = 4\pi r^2 \gamma$ surface free energy change positive

$4/3\pi r^3 \Delta G_V$ volume free energy change negative, l to s lowers energy

Direct Reactions of Solids

NUCLEATION RATE



r : radius of spheric seed

r^* : critical radius

($r > r^*$ seed grows by itself)

ΔG_N : total free energy change

ΔG_s : surface free energy change

ΔG_v : volume free energy change

$$\Delta G_N = 4\pi r^2 \gamma + \frac{4}{3} \pi r^3 \Delta G_v$$

Direct Reactions of Solids

Solidification

$$\Delta G = \frac{4}{3} \pi r^3 \Delta G_v + 4 \pi r^2 \gamma$$

- Volume free energy + surface energy

One solid phase changing to another

$$\Delta G = \frac{4}{3} \pi r^3 \Delta G_v + 4 \pi r^2 \gamma + \frac{4}{3} \pi r^3 \varepsilon$$

- Volume energy + surface energy + strain energy
- the new solid does not take up the same volume as the old solid

Nucleation versus crystal growth (solution or melt)

- relations between undercooling, nucleation and growth rate of the nuclei

large undercooling: many small nuclei

(spontaneous nucleation)

growth rate small

small undercooling: few (evtl. small) nuclei

growth rate high

DIRECT REACTION OF SOLIDS

NUCLEATION RATE

**Nucleation requires structural similarity of reactants and products
less reorganization energy = faster nucleation of product phase
within reactants**

MgO, Al₂O₃, MgAl₂O₄ example

**MgO (rock salt) and MgAl₂O₄ (spinel) similar ccp O²⁻
but distinct to hcp O²⁻ in Al₂O₃ phase**

Spinel nuclei, matching of structure at MgO interface

**Oxide arrangement essentially continuous across MgO/MgAl₂O₄
interface**

**Bottom line: structural similarity of reactants and products
promotes nucleation and growth of one phase within another**

Lattice of oxide anions, mobile Mg²⁺ and Al³⁺ cations

Topotactic and epitactic reactions

Orientation effects in the bulk and surface regions of solids

Implies structural relationships between reagent and product

Topotaxy occurs in bulk, 1-, 2- or 3-D

Epitaxy occurs at interfaces, 2-D

DIRECT REACTION OF SOLIDS

Epitactic reactions

require 2-D structural similarity, lattice matching within 15% to tolerate oriented nucleation otherwise mismatch over large contact area, strained interface, missing atoms

Example: MgO/BaO, both rock salt lattices, cannot be lattice matched over large contact area

Lattice matched crystalline growth

Best with less than 0.1% lattice mismatch. Causes elastic strain at interface

Slight atom displacement from equilibrium position.

Strain energy reduced by misfit-dislocation

Creates dangling bonds, localized electronic states, carrier scattering by defects, luminescence quenching, killer traps, generally reduces efficacy of electronic and optical devices, can be visualized by HR-TEM imaging

Direct Reactions of Solids

Topotactic reactions

More specific, require interfacial and bulk crystalline structural similarity, lattice matching

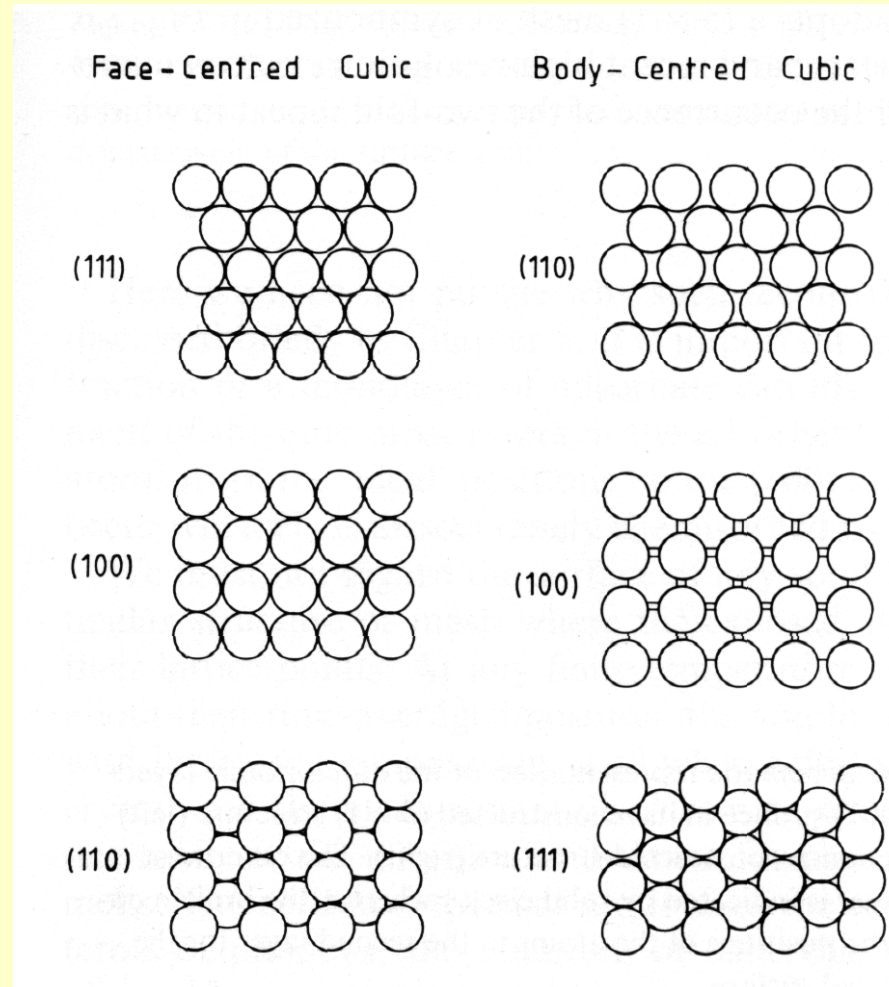
Topotaxy: involves lock-and-key ideas of self-assembly, molecule recognition, host-guest inclusion, clearly requires available space or creates space in the process of adsorption, injection, intercalation etc.

Direct Reactions of Solids

Surface structure and reactivity

Nucleation depends on actual surface structure of reacting phases.

Different Miller index faces exposed, atom arrangements different, different surface structures, implies distinct surface reactivities.

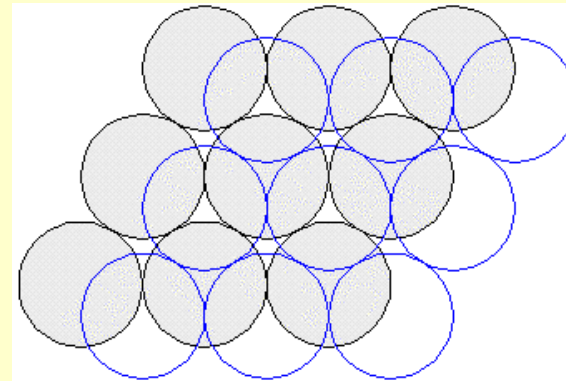
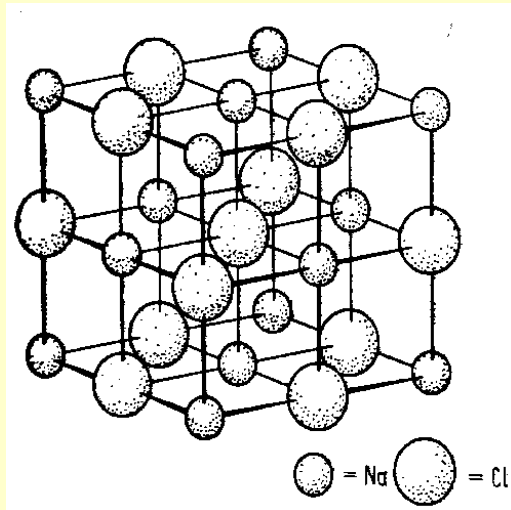


Direct Reactions of Solids

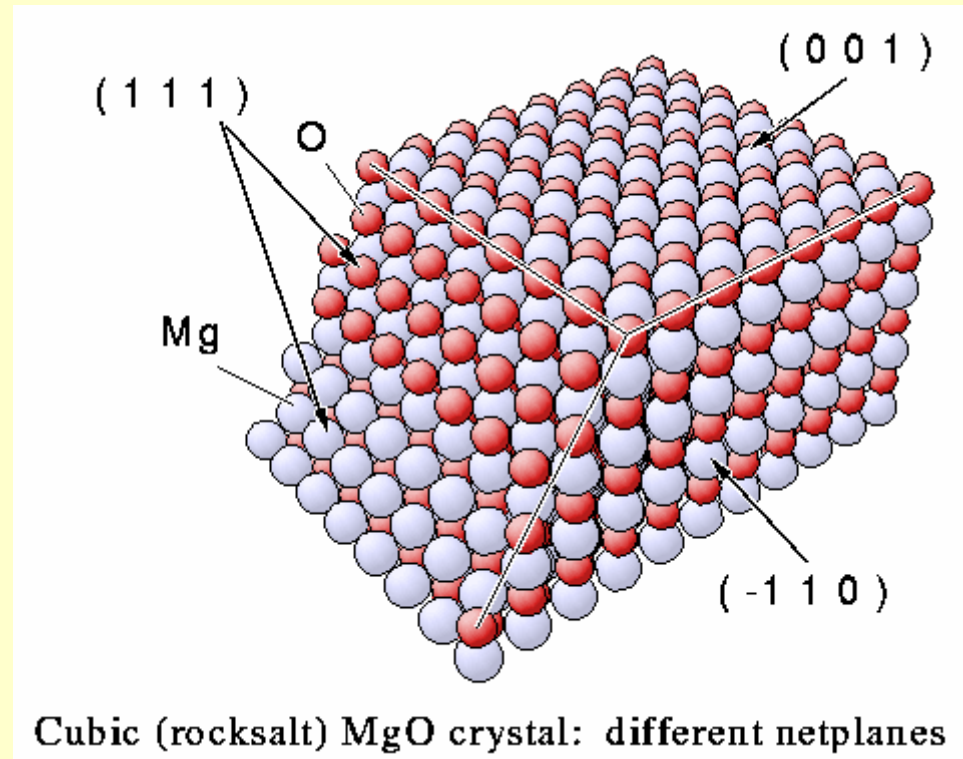
Example: MgO (rock salt)

{100} MgO alternating Mg^{2+} , O^{2-} at corners of square grid

{111} MgO, Mg^{2+} or O^{2-} hexagonal arrangement



Direct Reactions of Solids



Direct Reactions of Solids

Different crystal habits possible, depends on rate of growth of different faces, octahedral, cubooctahedral, cubic possible and variants in between

CRYSTAL GROWTH

Most prominent surfaces, slower growth

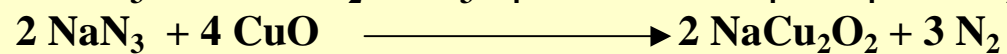
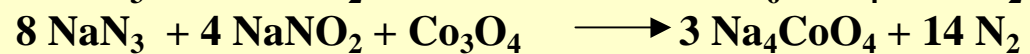
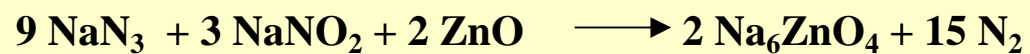
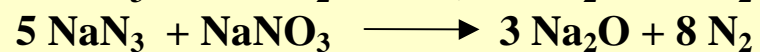
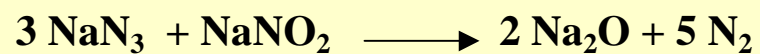
Growth rate of specific surfaces controls morphology

Depends on area of a face, structure of exposed face, accessibility of a face, adsorption at surface sites, surface defects

Play major role in reactivity, nucleation, crystal growth, materials properties (electronic, optical, magnetic, charge-transport, mechanical, thermal, acoustical etc)

DIRECT REACTION OF SOLIDS

Azide Method



DIRECT REACTION OF SOLIDS

Self-Sustained High-Temperature Synthesis (SHS)

Metal powders (Ti, Zr, Cr, Mo, W,) + other reactants

**mixing, pressing into pellets, ignition by energy pulse (W wire), S.S.
reactor, under Ar, exothermic, byproduct removal**

DIRECT REACTION OF SOLIDS

SHS reactions:

- * heterogeneous
- * exothermic, high temperatures, $T_f = 1500 - 3000 \text{ }^\circ\text{C}$
- * high thermal gradients
- * redox
- * frontal mode, reaction wave velocity $u = 1 - 10 \text{ mm.s}^{-1}$
- * metastable phases

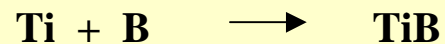
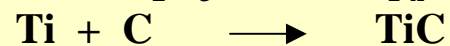
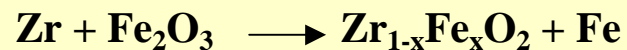
State of the substance in the reaction front:

solid ($T_f < T_m$, $p < p_0$) „solid flame“

liquid, melt ($T_f > T_m$)

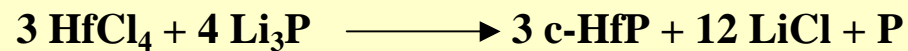
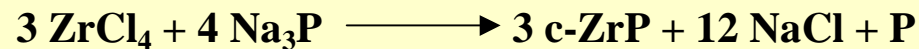
gaseous

Thermite reaction



Self-Propagating Metathesis

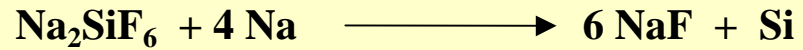
**Grinding of components in a glove box
addition of NaCl, KCl or NH₄Cl as a heat sink,
S.S. vessel, ignition by a resistively heated wire, reaction time 1 s,
washing products with MeOH, water, drying**



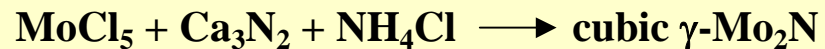
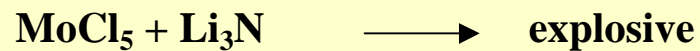
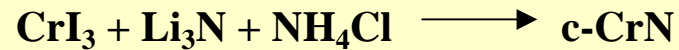
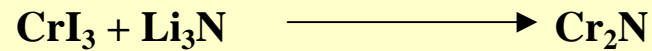
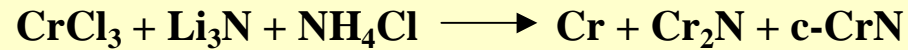
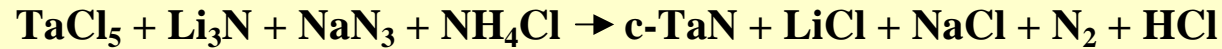
**c-ZrP and c-HfP hard and chemically inert materials,
hexagonal to cubic transitions: ZrP 1425 °C, HfP 1600 °C**

DIRECT REACTION OF SOLIDS

Silicon production

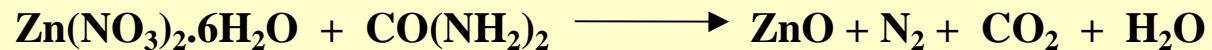


Hard materials production



Combustion Synthesis

**Oxidizing reagents (metal nitrates) mixed with fuel (urea, glycine) by
melting or in solution
drying
combustion ignited at 300-500 °C
exothermic self-propagating non-explosive reaction (excess of fuel)
reaction time 1 min, flame temperature 1000 °C
product dry foam, crumbles to a fine powder.**

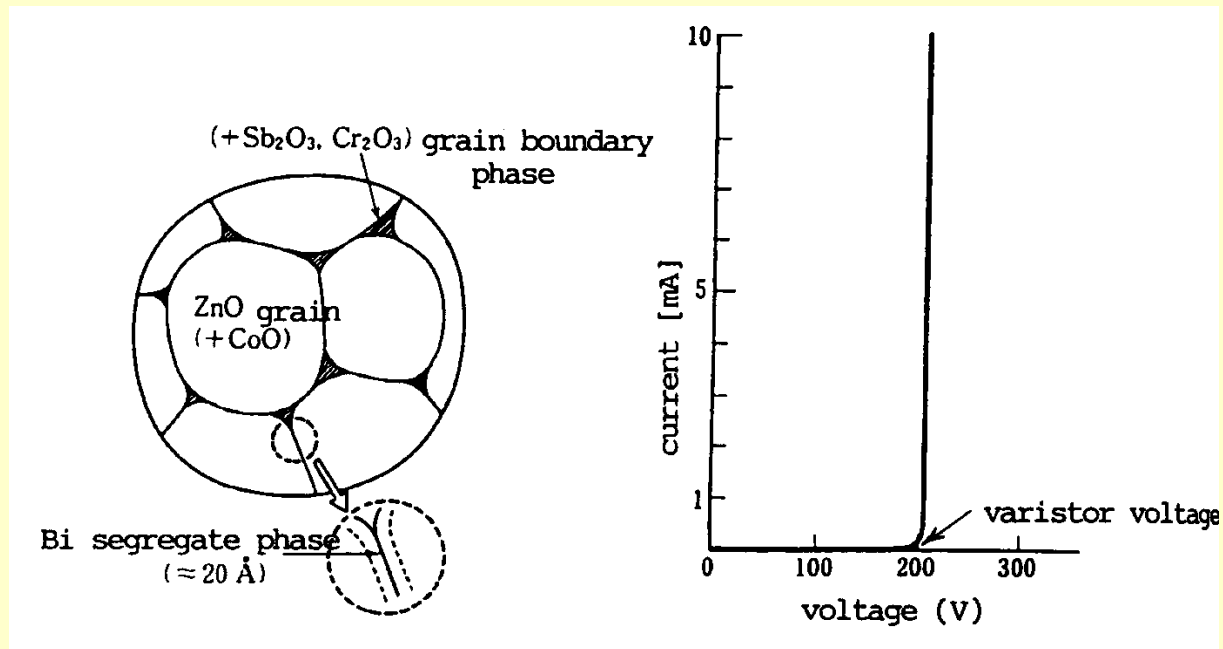


Combustion Synthesis

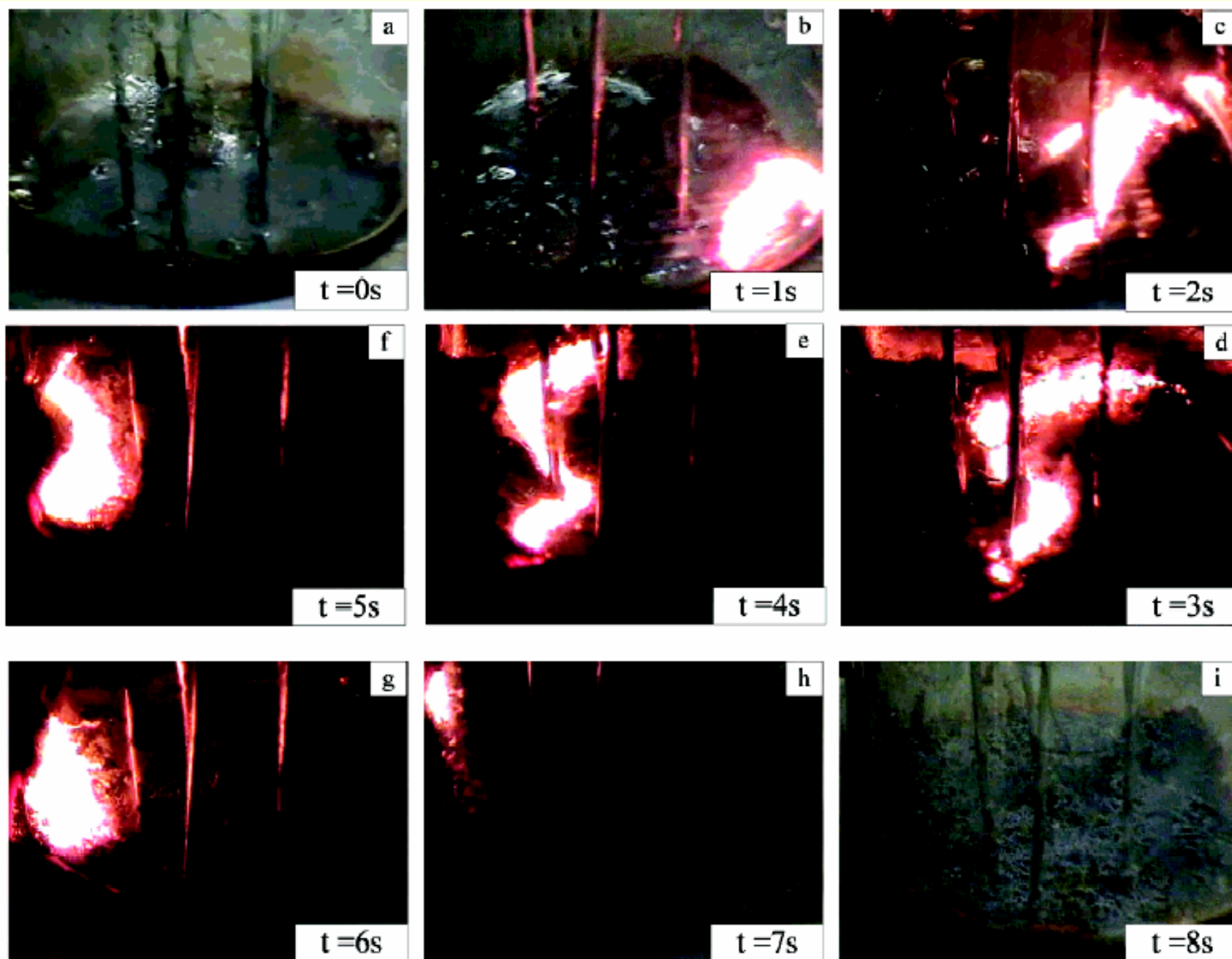
Examples

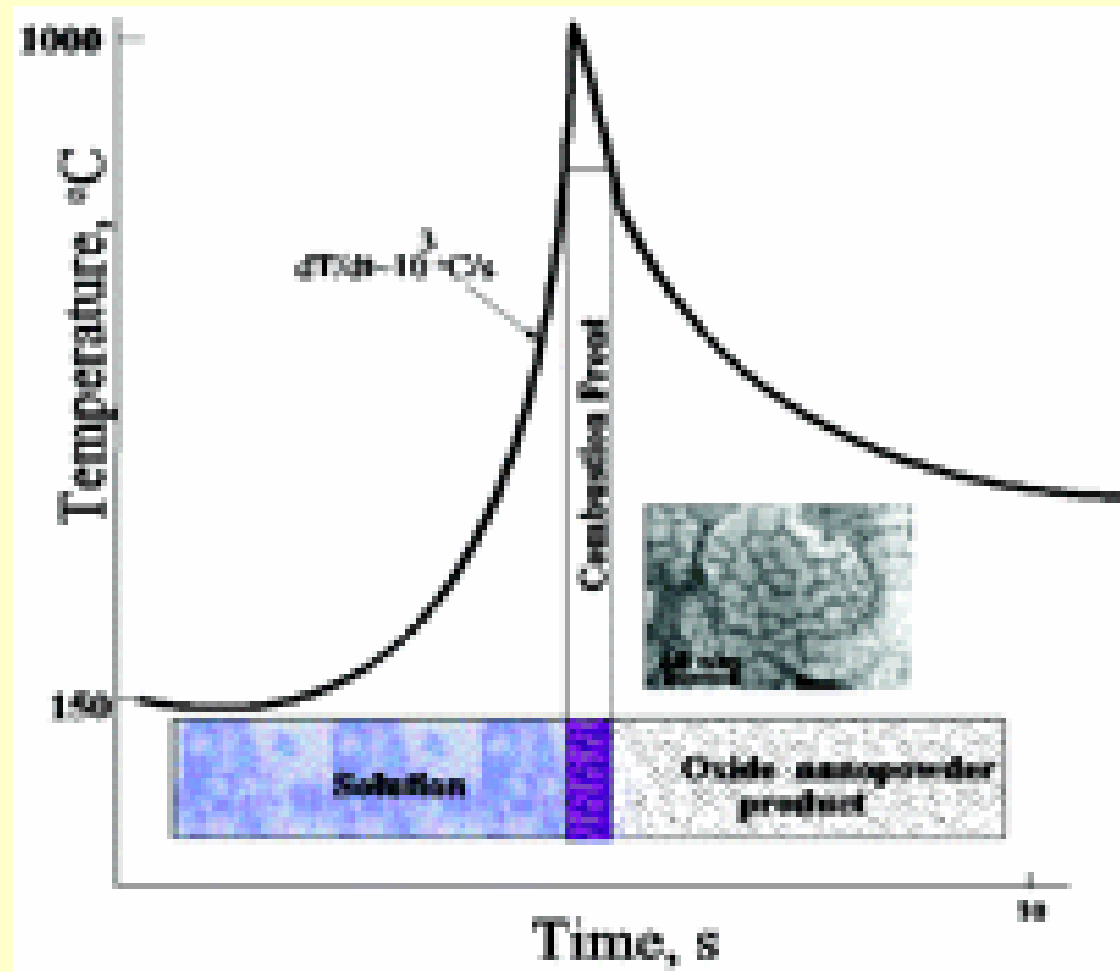
ZnO(90%) - Bi₂O₃ - Sb₂O₃

Non-Ohmic behavior $I = (U/C)^a$ C, a = constants, a = 50
Voltage stabilization, surge absorption



Reaction front propagation: glycine-iron nitrate





Combustion Synthesis

Examples



mixing 1:1:1 in aqueous solution, drying at 90 °C

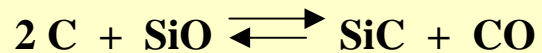
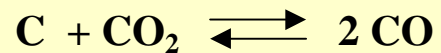
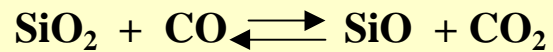
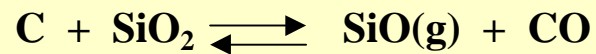
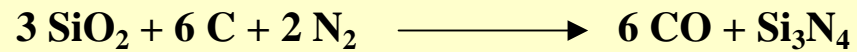
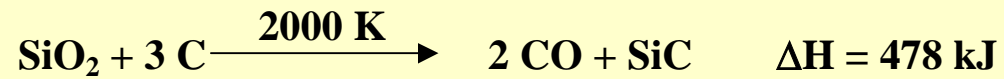
combustion at 250 °C

calcination to LiVMoO₆ cathode material for Li-ion

DIRECT REACTION OF SOLIDS

Carbothermal Reduction

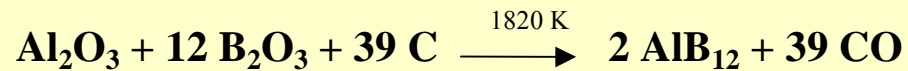
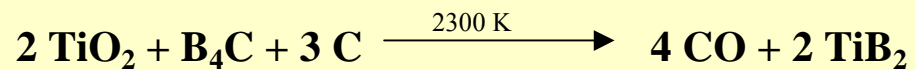
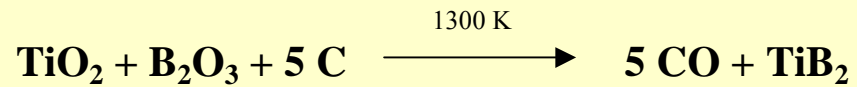
Acheson



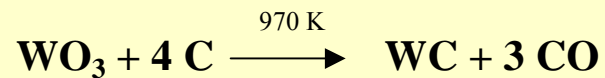
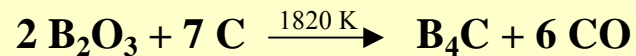
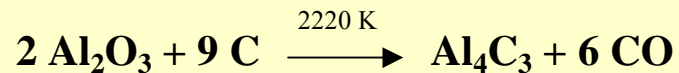
DIRECT REACTION OF SOLIDS

Carbothermal Reduction

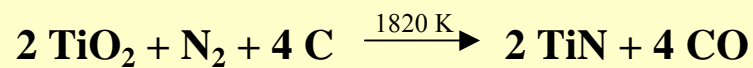
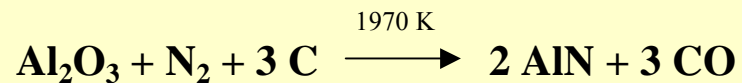
Borides



Carbides



Nitrides



DIRECT REACTION OF SOLIDS

Fusion-Crystallization from Glass

Mixing powders

Melting to glass: single phase, homogeneous (T, C), amorphous

Temperature limits: **mp of reagents**
 volatility of reagents

Nucleation agent

Homogeneous nucleation, few crystal seeds

Slow transport of precursors to seed

Lowest possible crystallization temperature

Crystallizing a glass above its glass transition

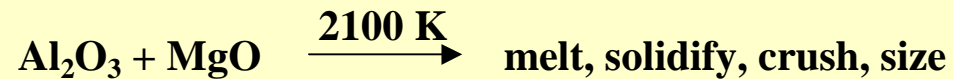
Metastable phases accessible, often impossible to prepare by other methods

DIRECT REACTION OF SOLIDS

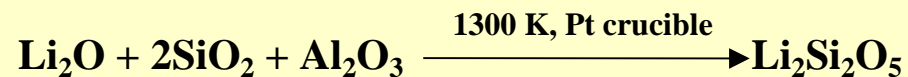
Fusion-Crystallization from Glass

Production of window glass

Abrasive grains



Crystallizing an inorganic glass, lithium disilicate



$\text{Li}_2\text{Si}_2\text{O}_5$ forms as a melt. Hold at 1100°C for 2-3 hrs. Homogeneous, rapid cooling, fast viscosity increase, quenches transparent glass

$\text{Li}_2\text{Si}_2\text{O}_5$, glass 500-700°C, $T_g \sim 450^\circ\text{C}$ from DSC \rightarrow $\text{Li}_2\text{Si}_2\text{O}_5$, crystals in 2-3 hrs., principle of crystallizing a glass above its glass transition

DIRECT REACTION OF SOLIDS

Fusion-Crystallization from Glass

Glass Ceramics

polyxtalline materials made by controlled xtallization of glasses

Cooking utensils

$\text{Li}_2\text{O}/\text{SiO}_2/\text{Al}_2\text{O}_3(>10\%)$ nucl. TiO_2 β -spodumene

Vacuum tube components

$\text{Li}_2\text{O}/\text{SiO}_2/\text{Al}_2\text{O}_3(<10\%)$ nucl. P_2O_5 Li-disilicate, quartz

Missile radomes

$\text{MgO}/\text{SiO}_2/\text{Al}_2\text{O}_3$ nucl. TiO_2 cordierite, cristobalite